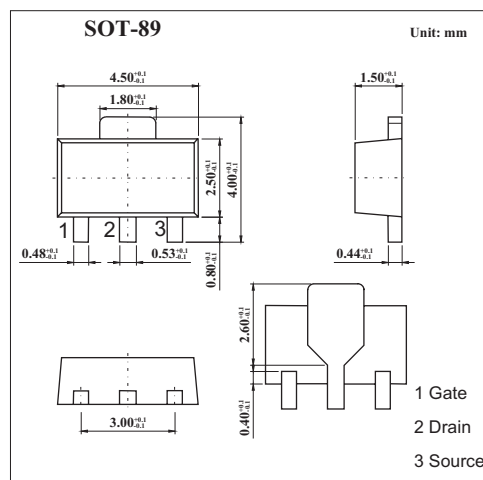
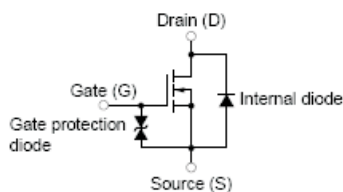


2SK2111

■ Features

- Low on-resistance
R_{DS(on)}=0.6 Ω MAX.@V_{GS}=4.0V,I_D=0.5A
- High switching speed



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	±1.0	A
	I _{DP}	±2.0	A
Power dissipation *	P _D	2.0	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* 16 cm²X0.7mm,ceramic substrate used

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Drain cut-off current	I _{DSS}	V _{DS} =60V,V _{GS} =0			1.0	μ A	
Gate leakage current	I _{GSS}	V _{GS} =±20V,V _{DS} =0			±10	μ A	
Gate threshold voltage	V _{GS(th)}	V _{DS} =10V,I _D =1mA	0.8	1.4	2.0	V	
Forward transfer admittance	Y _{fs}	V _{DS} =10V,I _D =0.5A	0.4			S	
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =4.0V,I _D =0.5A		0.32	0.6	Ω	
		V _{GS} =10V,I _D =0.5A		0.24	0.45	Ω	
Input capacitance	C _{iss}	V _{DS} =10V,V _{GS} =0,f=1MHZ		170		pF	
Output capacitance	C _{oss}			87		pF	
Reverse transfer capacitance	C _{rss}			32		pF	
Turn-on delay time	t _{d(on)}				2.8		ns
Rise time	t _r	I _D =0.5A,V _{GS(on)} =10V,R _L =50 Ω ,R _G =10 Ω ,V _{DD} =25V		2.3		ns	
Turn-off delay time	t _{d(off)}				55		ns
Fall time	t _f				27		ns

■ Marking

Marking	NU
---------	----